Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in an ultra small DFN1110D-3 (SOT8015) leadless Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic-level compatible
- Side wettable flanks for optical solder inspection
- Ultra small and leadless SMD plastic package: 1.1 x 1 x 0.48 mm
- · Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 1 kV HBM (Class H1C)
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- · Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V	
V_{GS}	gate-source voltage			-16	-	16	V	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	720	mA	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 720 \text{ mA}; T_j = 25 \text{ °C}$		-	635	850	mΩ	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source	3	
3	D	drain	Transparent top view DFN1110D-3 (SOT8015)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
2N7002KQB		plastic, leadless extremely thin small outline package with side-wettable flanks (SWF); 3 terminals; 0.65 mm pitch; 1.1 mm x 1 mm x 0.48 mm body	SOT8015			

7. Marking

Table 4. Marking codes

Type number	Marking code
2N7002KQB	C7

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-16	16	V
V_{GSMlim}	peak gate-source voltage	$\delta_{factor} = 0.1; t_p = 50 \ \mu s; T_j = 25 \ ^{\circ}C$		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	720	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	460	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	2.9	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	420	mW
			[1]	-	960	mW
		T _{sp} = 25 °C		-	4.2	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode				,	
Is	source current	T _{amb} = 25 °C	[1]	-	700	mA
ESD maximu	m rating				'	
V _{ESD}	electrostatic discharge voltage	НВМ		-	1000	V
Avalanche ru	ıggedness		•	'	•	'
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)} = 25 ^{\circ}C; I_{D} = 0.05 A$		-	1.5	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

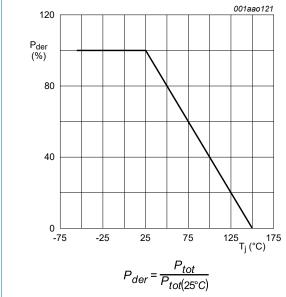


Fig. 1. Normalized total power dissipation as a function of junction temperature

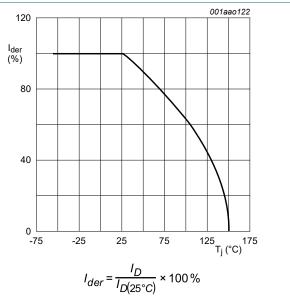


Fig. 2. Normalized continuous drain current as a function of junction temperature

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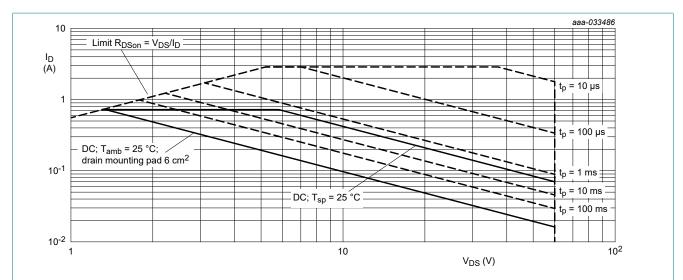


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

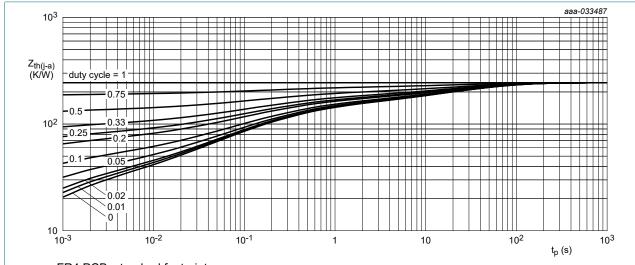
60 V N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

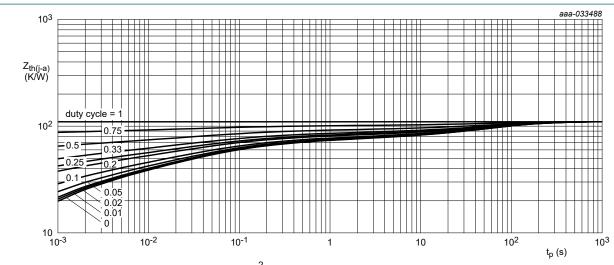
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	245	300	K/W
junction	junction to ambient	ction to ambient	[2]	-	110	130	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	25	30	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.3	1.7	2.6	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 720 mA; T _j = 25 °C	-	635	850	mΩ
	resistance	V _{GS} = 10 V; I _D = 720 mA; T _j = 150 °C	-	1400	1800	mΩ
		V _{GS} = 4.5 V; I _D = 630 mA; T _j = 25 °C	-	765	1100	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 720 \text{ mA}; T_j = 25 \text{ °C}$	-	1.1	-	S
Dynamic ch	naracteristics					1
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 0.7 \text{ A}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}$	-	0.61	0.92	nC
Q _{GS}	gate-source charge		-	0.07	-	nC
Q _{GD}	gate-drain charge		-	0.15	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	28	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	5	-	pF
C _{rss}	reverse transfer capacitance		-	3	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; I _D = 0.7 A; V _{GS} = 10 V;	-	1	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	1	-	ns
t _{d(off)}	turn-off delay time		-	6	-	ns
t _f	fall time]	-	3	-	ns
Source-dra	in diode		1	_		
V _{SD}	source-drain voltage	I _S = 0.7 A; V _{GS} = 0 V; T _j = 25 °C	-	0.7	1.2	V
t _{rr}	reverse recovery time	I _S = 0.7 A; dI _S /dt = -100 A/s; V _{GS} = 10 V; V _{DS} = 30 V; T _j = 25 °C	-	8	-	ns
Q _r	recovered charge	I _S = 0.7 A; dI _S /dt = -100 A/μs; V _{GS} = 10 V; V _{DS} = 30 V; T _i = 25 °C	-	2	-	nC

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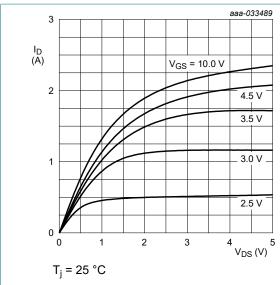


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

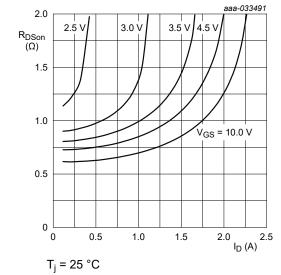


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

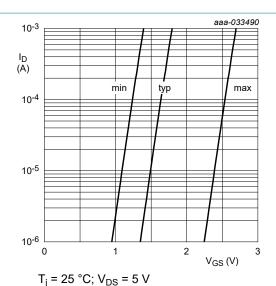


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

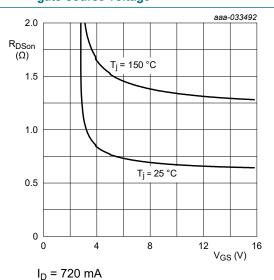


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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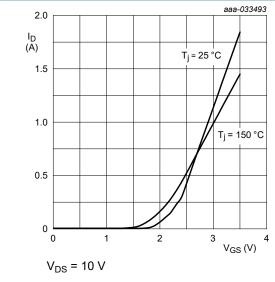


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

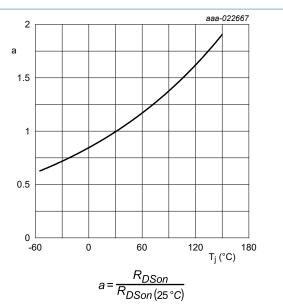


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

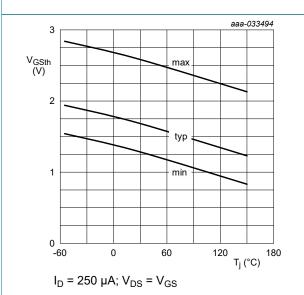
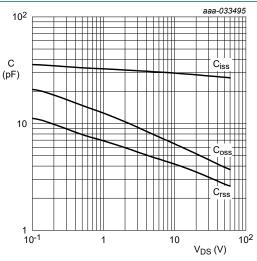


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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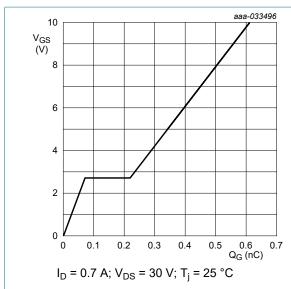


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

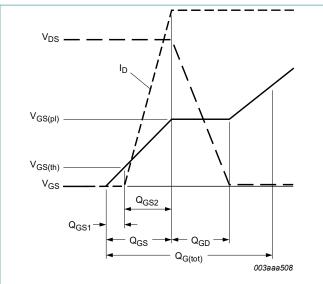


Fig. 15. Gate charge waveform definitions

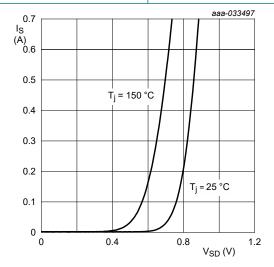
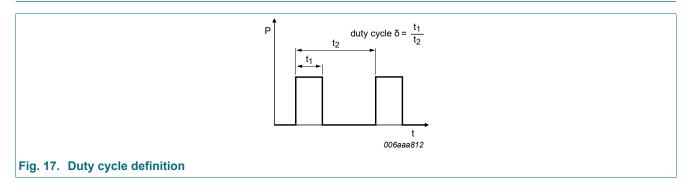


Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

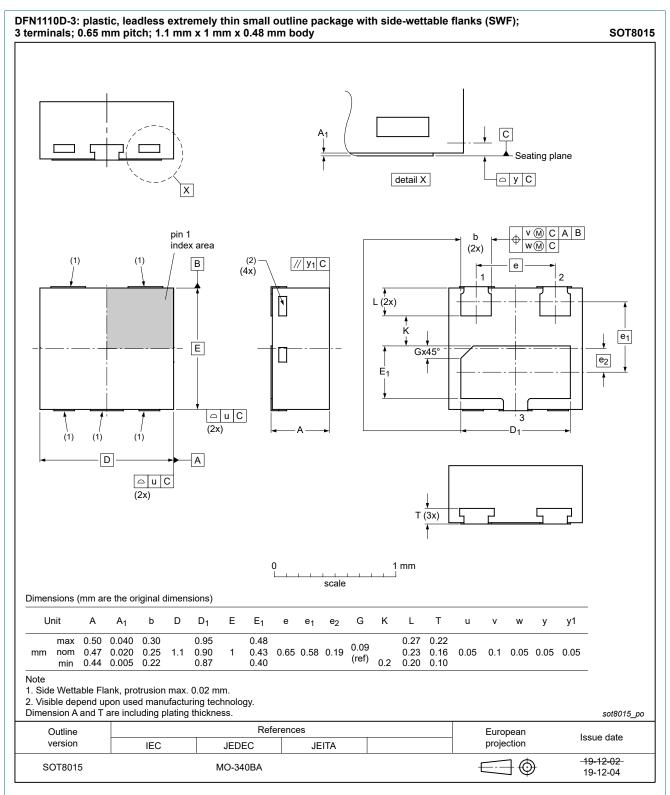
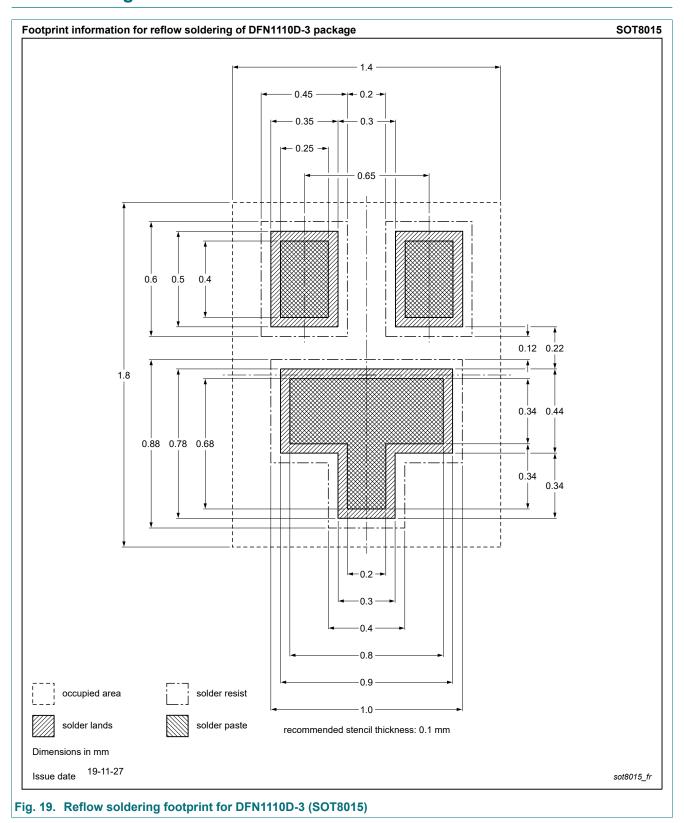


Fig. 18. Package outline DFN1110D-3 (SOT8015)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
2N7002KQB v.1	20210922	Product data sheet	-	-

60 V N-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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